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IGBT

FGL60N100D

General Description

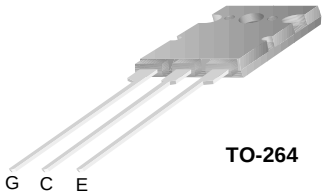
Insulated Gate Bipolar Transistors (IGBTs) with trench gate structure have superior performance in conduction and switching to planar gate structure, and also have wide noise immunity. These devices are well suitable for IH applications

Features

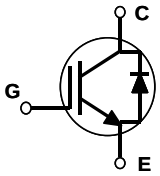
- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)}$ = 2.5V @ I_C = 60A
- High Input Impedance
- Built-in Fast Recovery Diode

Application

Home Appliance, Induction Heater, IH JAR, Micro Wave Oven



TO-264



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Description		FGL60N100D	Units
V_{CES}	Collector-Emitter Voltage		1000	V
V_{GES}	Gate-Emitter Voltage		± 25	V
I_C	Collector Current	@ T_C = 25°C	60	A
	Collector Current	@ T_C = 100°C	42	A
$I_{CM\ (1)}$	Pulsed Collector Current		120	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	15	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	176	W
	Maximum Power Dissipation	@ T_C = 100°C	70	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes :
(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction-to-Case	--	0.71	°C/W
$R_{\theta JC}$(DIODE)	Thermal Resistance, Junction-to-Case	--	2.08	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	25	°C/W

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Electrical Characteristics of IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
I_{CES}	Collector Cut-Off Current	V_{CE} = 1000V, V_{GE} = 0V	--	--	1.0	mA
I_{GES}	G-E Leakage Current	V_{GE} = ± 25, V_{CE} = 0V	--	--	± 500	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 60mA, V_{CE} = V_{GE}	4.0	5.0	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 10A, V_{GE} = 15V	--	1.6	2.0	V
		I_C = 60A, V_{GE} = 15V	--	2.5	2.9	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE}=10V, V_{GE} = 0V, f = 1MHz	--	6300	--	pF
C_{oes}	Output Capacitance		--	160	--	pF
C_{res}	Reverse Transfer Capacitance		--	140	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600V, I_C = 60A, R_G = 51Ω, V_{GE}=15V, Resistive Load, T_C = 25°C	--	160	400	ns
t_r	Rise Time		--	360	700	ns
$t_{d(off)}$	Turn-Off Delay Time		--	410	700	ns
t_f	Fall Time		--	240	330	ns
Q_g	Total Gate Charge	V_{CE} = 600 V, I_C = 60A, V_{GE} = 15V	--	230	300	nC
Q_{ge}	Gate-Emitter Charge		--	45	--	nC
Q_{gc}	Gate-Collector Charge		--	80	--	nC

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	I_F = 15A	--	1.2	1.7	V
		I_F = 60A	--	1.8	2.1	V
t_{rr}	Diode Reverse Recovery Time	I_F = 60A di/dt = -20A/us		1.2	1.5	us
I_R	Instantaneous Reverse Current	V_{RRM} = 1000V	--	0.05	2	uA

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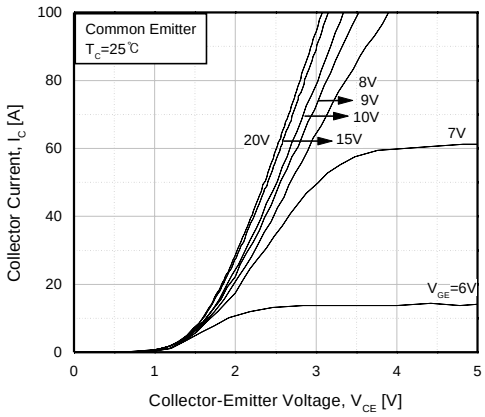


Fig 1. Typical Output Characteristics

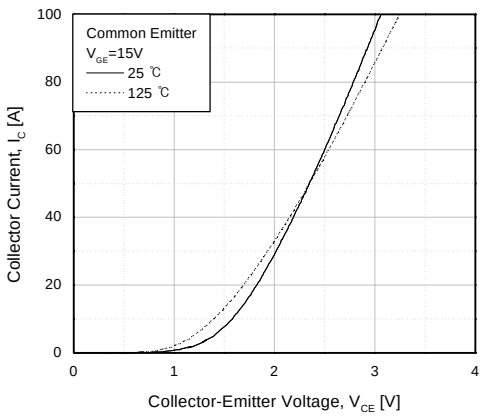


Fig 2. Typical Saturation Voltage Characteristics

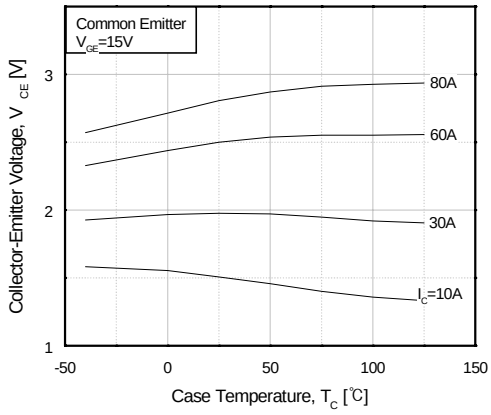


Fig 3. Saturation Voltage vs. Case Temperature at Varient Current Level

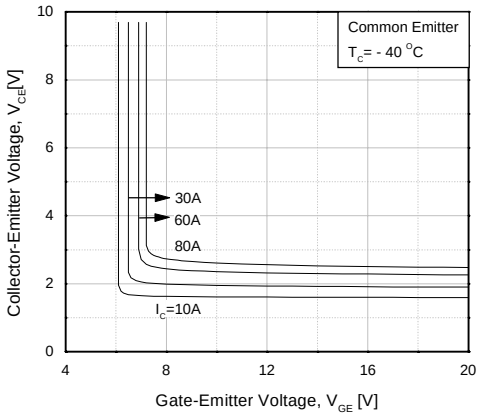


Fig 4. Saturation Voltage vs. V_{GE}

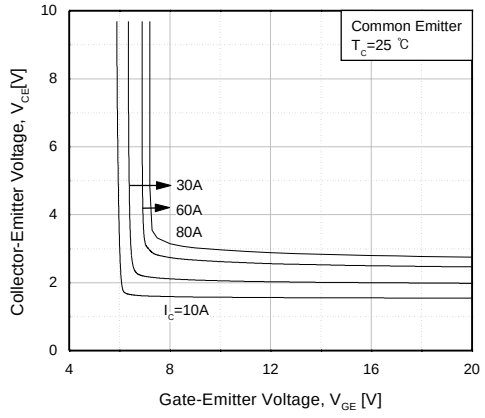


Fig 5. Saturation Voltage vs. V_{GE}

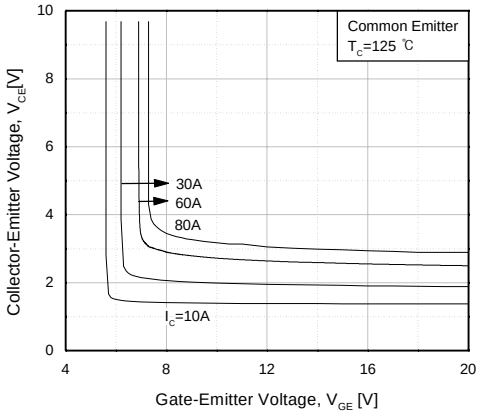


Fig 6. Saturation Voltage vs. V_{GE}

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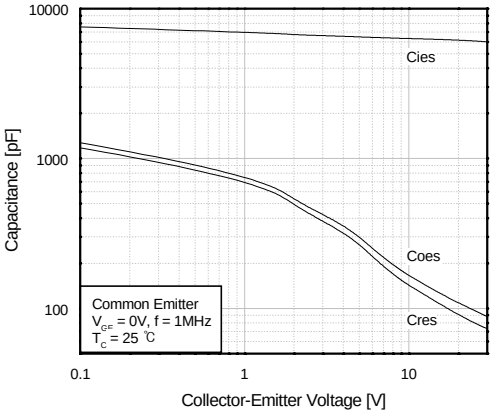


Fig 7. Capacitance Characteristics

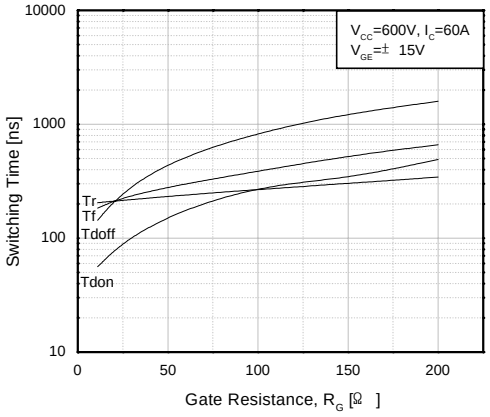


Fig 8. Switching Characteristics vs. Gate Resistance

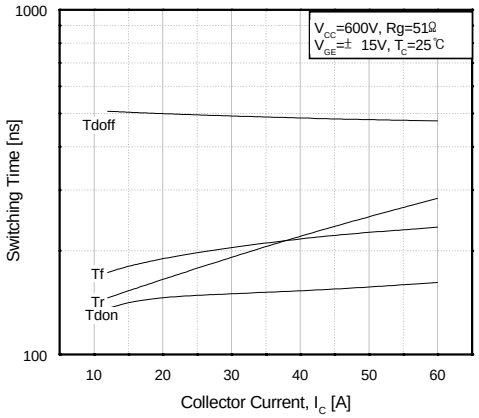


Fig 9. Switching Characteristics vs. Collector Current

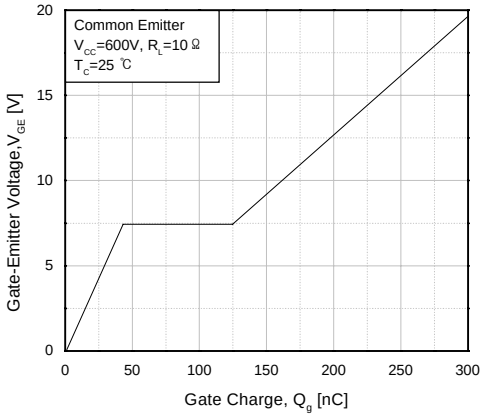


Fig 10. Gate Charge Characteristics

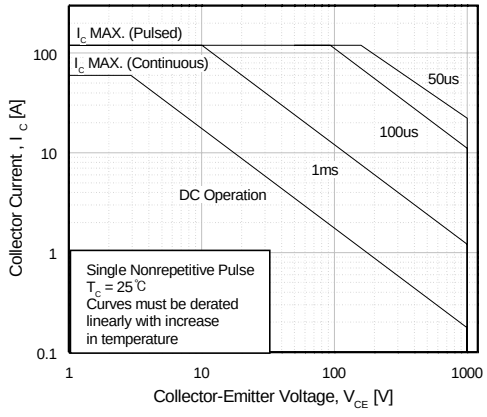


Fig 11. SOA Characteristics

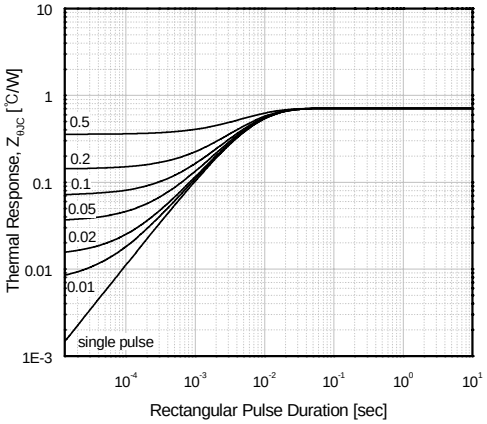


Fig 12. Transient Thermal Impedance of IGBT

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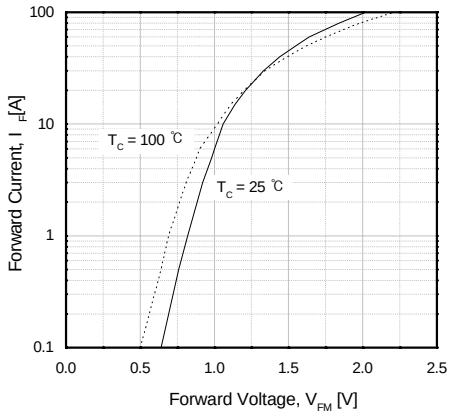


Fig 13. Forward Characteristics

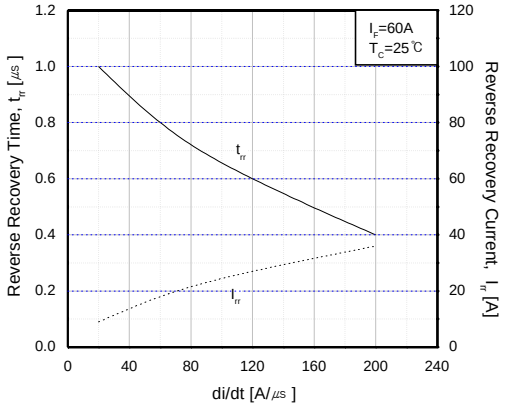


Fig 14. Reverse Recovery Characteristics vs. di/dt

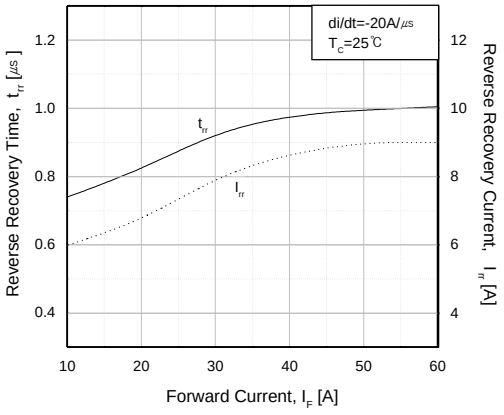


Fig 15. Reverse Recovery Characteristics vs. Forward Current

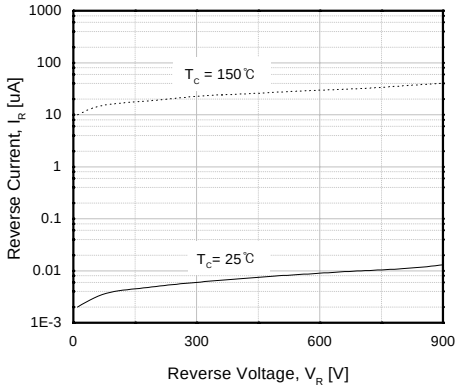


Fig 16. Reverse Current vs. Reverse Voltage

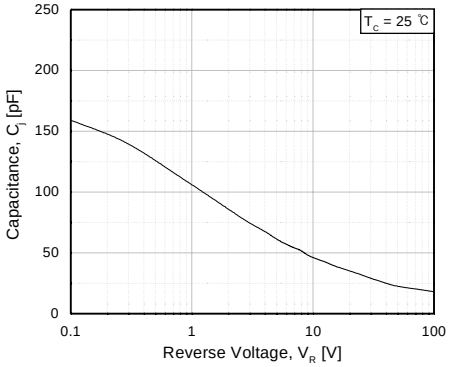


Fig 17. Junction capacitance

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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